

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

BLY91C

BLY91C is Designed for
 28 V Large Signal Class A,B and C
 Amplifier Applications up to 175 MHz.

FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- 3/8" SOE Stud Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	35 V
V_{CB}	65 V
P_{DISS}	20 W @ $T_C = 25^\circ C$
T_J	-65 °C to + 200 °C
T_{STG}	-65 °C to + 150 °C
θ_{JC}	8.7 °C/W

PACKAGE STYLE .380" 4L STUD

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/.559	.240/.614
B	.980/.2489	
C	.370/.940	.385/.978
D	.004/.101	.007/.178
E	.320/.813	.330/.838
F	.180/.454	.180/.454
G	.450/.1143	.438/.11245
H	.090/.229	.100/.254
I	.157/.394	.175/.445
J		.750/.1905

1 = COLLECTOR 2 & 4 = EMITTER
 3 = BASE

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200 \text{ mA}$	65			V
BV_{CEO}	$I_C = 10 \text{ mA}$	35			V
BV_{EBO}	$I_E = 1.0 \text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 36 \text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0 \text{ V}$ $I_C = 400 \text{ mA}$	10		100	---
C_{OB}	$V_{CB} = 30 \text{ V}$ $f = 1.0 \text{ MHz}$			15	pF
P_G	$V_{CC} = 28 \text{ V}$ $P_{OUT} = 8.0 \text{ W}$ $f = 175 \text{ MHz}$	12.0	13.0		dB
η_c		65			%

